L Number	Hits	Search Text	DB	Time stamp
Number 1	818	438/264	USPAT;	2002/03/08
1 /	010	130/ 201	US-PGPUB; /	15:08
`			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	137	257/46	USPAT;	2002/03/08
2	13,	2017.10	US-PGPUB;	15:24
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	58971	method adj producing.ti.	USPAT;	2002/03/08
3	303,1		US-PGPUB;	15:09
			EPO; JPO;	***
			DERWENT;	ĺ
			IBM TDB	
4	10	(method adj producing.ti.) adj	USPAT;	2002/03/08
4	10	oxidation.ti.	US-PGPUB;	15:10
		ONLUG DISTORT	EPO; JPO;	
			DERWENT;	
			IBM TDB	
6	175	"capacitive electrode".ti.	USPAT;	2002/03/08
O	1,0	oupuon sa	US-PGPUB;	15:37
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
11	13	"capacitive electrode structure"	USPAT;	2002/03/08
11	13	Capacitation of the capaci	US-PGPUB;	15:13
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
13	6	"capacitive electrode structure" and	USPAT;	2002/03/08
13		semiconductor	US-PGPUB;	15:13
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
14	1	("capacitive electrode structure" and	USPAT;	2002/03/08
	_	semiconductor) and oxidation	US-PGPUB;	15:14
		,	EPO; JPO;	
			DERWENT;	
	]		IBM_TDB	
15	2088	(semiconductor adj substrate) adj5	USPAT;	2002/03/08
		oxidation	US-PGPUB;	15:31
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
16	1	((semiconductor adj substrate) adj5	USPAT;	2002/03/08
1	_	oxidation) adj5 "metal oxide layer"	US-PGPUB;	15:16
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
17	1		USPAT;	2002/03/08
l	1	oxidation) same "metal oxide layer"	US-PGPUB;	15:16
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
18	32	((semiconductor adj substrate) adj5	USPĀT;	2002/03/08
		oxidation) same "metal oxide"	US-PGPUB;	15:16
1		·	EPO; JPO;	1
			DERWENT;	
			IBM_TDB	
21	10	(((semiconductor adj substrate) adj5	USPAT;	2002/03/08
		oxidation) same "metal oxide") same	US-PGPUB;	15:17
		"conductive"	EPO; JPO;	
			DERWENT;	
	I .	1	IBM TDB	1

8	11	"capacitive electrode".ti. and "method".ti.	USPAT; US-PGPUB;	2002/03/08 15:18
			EPO; JPO; DERWENT; IBM_TDB	
10	7	"capacitive electrode".ti. and dram.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/08
23	1	((((semiconductor adj substrate) adj5 oxidation) same "metal oxide") same "conductive") and tungsten	USPĀT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/08 15:20
25	1	((semiconductor adj substrate) adj5 oxidation) and "electrical conductive"	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/08 15:22
26	22	"metal oxide layer" and "electrical conductive"	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/08
28	1	("metal oxide layer" and "electrical conductive") and capacitor	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/08 15:23
30	1	(("metal oxide layer" and "electrical conductive") and semiconductor) and tungsten	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/08 15:23
29	7	("metal oxide layer" and "electrical conductive") and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/08 15:24
32	116	((semiconductor adj substrate) adj5 oxidation) same ("metal oxide layer" or mos)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/08
34	2	((((semiconductor adj substrate) adj5 oxidation) same ("metal oxide layer" or mos)) same (conductive or conductor)) and tungsten	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/08 15:26
33	15	(((semiconductor adj substrate) adj5 oxidation) same ("metal oxide layer" or mos)) same (conductive or conductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/08
35	3142	(semiconductor adj substrate) near5 oxidation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/08
36	2	((semiconductor adj substrate) near5 oxidation) near5 "metal oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/08
37	47	((semiconductor adj substrate) near5 oxidation) same "metal oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/08

			USPAT;	2002/03/08
38	9	(((semiconductor adj substrate) near5	USPAT; US-PGPUB;	15:35
		oxidation) same "metal oxide") same	EPO; JPO;	15.55
ļ		electrode	·	
			DERWENT;	
			IBM_TDB	2002/03/08
39	1	((((semiconductor adj substrate) near5	USPAT;	
		oxidation) same "metal oxide") same	US-PGPUB;	15:35
		electrode) same conductive	EPO; JPO;	
			DERWENT;	
		_	IBM_TDB	
40	1	((((semiconductor adj substrate) near5	USPAT;	2002/03/08
		oxidation) same "metal oxide") same	US-PGPUB;	15:36
		electrode) same (conductive or conductor)	EPO; JPO;	
		~~	DERWENT;	1
ļ į			IBM_TDB	
41	977	"capacitive electrode"	USPAT;	2002/03/08
			US-PGPUB;	15:38
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
42	5	((semiconductor adj substrate) adj5	USPAT;	2002/03/08
		oxidation) and "capacitive electrode"	US-PGPUB;	15:40
		· •	EPO; JPO;	
			DERWENT;	
			IBM_TDB	1
43	1	krasemann-anke.in.	USPAT;	2002/03/08
33	-		US-PGPUB;	15:40
			EPO; JPO;	
			DERWENT;	
.			IBM TDB	
44	0	krasemann-anke-\$.in.	USPAT;	2002/03/08
44		Alagemaini dinc v.iii.	US-PGPUB;	15:40
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
145	1	pompl-thomas.in.	USPAT;	2002/03/08
45	1	pompi-chomas.in.	US-PGPUB;	15:41
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
4.6	0	pompl-thomas-\$.in.	USPAT;	2002/03/08
46	"	pompi-thomas-3.in.	US-PGPUB;	15:41
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
47	37	huama-martin in	USPAT;	2002/03/08
47	3/	schrems-martin.in.	US-PGPUB;	15:41
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
1.0	_	lankana mantin 6 in	USPAT;	2002/03/08
48	3	schrems-martin-\$.in.	US-PGPUB;	15:41
			EPO; JPO;	1
			DERWENT;	
	1		IBM TDB	
1	_	A des	USPAT;	2002/03/08
49	0	wurzer-helmut-\$.in.	US-PGPUB;	15:41
	1			13.31
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	2002/02/05
50	9	wurzer-helmut.in.	USPAT;	2002/03/08
			US-PGPUB;	15:41
			EPO; JPO;	
1			DERWENT;	
	I .		IBM TDB	1